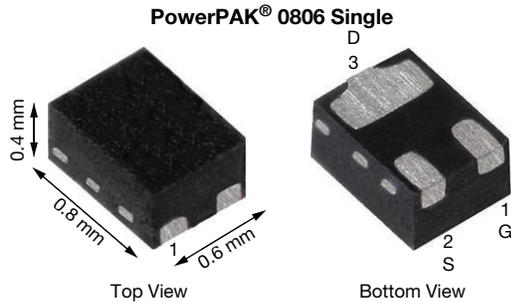


P-Channel 20 V (D-S) MOSFET



FEATURES

- TrenchFET® Gen III p-channel power MOSFET
- Ultra small 0.8 mm x 0.6 mm outline
- Ultra thin 0.4 mm max. height
- Typical ESD protection 1500 V (HBM)
- -1.5 V rated $R_{DS(ON)}$
- 100% R_g tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

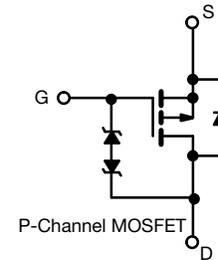


RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY	
V_{DS} (V)	-20
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5$ V	1.25
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -2.5$ V	1.7
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.8$ V	2.7
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.5$ V	4.4
Q_g typ. (nC)	0.64
I_D (A)	-0.5 ^{a, f}
Configuration	Single

APPLICATIONS

- Load switch
- High speed switching
- Power management in battery-operated, mobile and wearable devices



ORDERING INFORMATION	
Package	PowerPAK 0806
Lead (Pb)-free and halogen-free	SiUD403ED-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	-20	V	
Gate-source voltage	V_{GS}	± 8	V	
Continuous drain current ($T_J = 150$ °C)	I_D	$T_A = 25$ °C	-0.5 ^{a, f}	A
		$T_A = 70$ °C	-0.5 ^{a, f}	
		$T_A = 25$ °C	-0.4 ^b	
		$T_A = 70$ °C	-0.32 ^b	
Pulsed drain current ($t = 100$ μ s)	I_{DM}	-0.8	A	
Continuous source-drain diode current	I_S	$T_A = 25$ °C	-0.5 ^{a, f}	A
		$T_A = 70$ °C	-0.37 ^b	
Maximum power dissipation	P_D	$T_A = 25$ °C	1.25 ^a	W
		$T_A = 70$ °C	0.8 ^a	
		$T_A = 25$ °C	0.37 ^b	
		$T_A = 70$ °C	0.24 ^b	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature) ^c		260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^{a, d}	R_{thJA}	80	100	°C/W
Maximum junction-to-ambient ^{b, e}		265	335	

Notes

- Surface mounted on 1" x 1" FR4 board with full copper, $t = 5$ s.
- Surface mounted on 1" x 1" FR4 board with minimum copper, $t = 5$ s.
- Refer to IPC / JEDEC® (J-STD-020), no manual or hand soldering.
- Maximum under steady state conditions is 135 °C/W.
- Maximum under steady state conditions is 400 °C/W.
- Package limited.



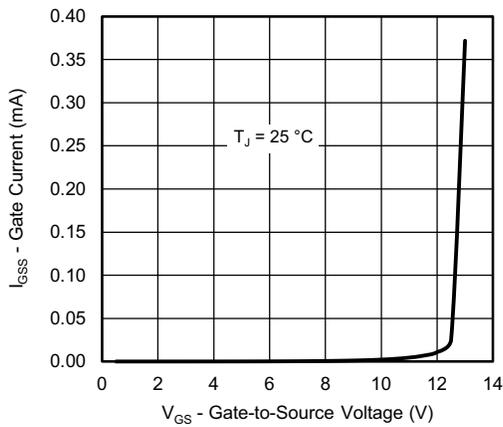
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA	-20	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	I _D = -250 μA	-	-12.4	-	mV/°C
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J		-	1.6	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.4	-	-0.9	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 4.5 V	-	-	± 0.5	μA
		V _{DS} = 0 V, V _{GS} = ± 8 V	-	-	± 7	
Zero gate voltage drain current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V	-	-	-1	μA
		V _{DS} = -20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-10	
On-state drain current ^a	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = 0 V	-0.5	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -4.5 V, I _D = -0.3 A	-	1.01	1.25	Ω
		V _{GS} = -2.5 V, I _D = -0.1 A	-	1.4	1.7	
		V _{GS} = -1.8 V, I _D = -0.1 A	-	2.1	2.7	
		V _{GS} = -1.5 V, I _D = -0.05 A	-	2.8	4.4	
Forward transconductance ^a	g _{fs}	V _{DS} = -10 V, I _D = -0.3 A	-	0.6	-	S
Dynamic ^b						
Input capacitance	C _{ISS}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	-	31	-	pF
Output capacitance	C _{OSS}		-	8.1	-	
Reverse transfer capacitance	C _{RSS}		-	7	-	
Total gate charge	Q _g	V _{DS} = -10 V, V _{GS} = -8 V, I _D = -0.3 A	-	1.1	1.7	nC
		V _{DS} = -10 V, V _{GS} = -4.5 V, I _D = -0.3 A	-	0.64	1	
Gate-source charge	Q _{gs}	V _{DS} = -10 V, V _{GS} = -4.5 V, I _D = -0.3 A	-	0.13	-	
Gate-drain charge	Q _{gd}		-	0.1	-	
Gate resistance	R _g	f = xx MHz	15	74	150	Ω
Turn-on delay time	t _{d(on)}	V _{DD} = -10 V, R _L = 33.3 Ω, I _D ≅ -0.3 A, V _{GEN} = -4.5 V, R _g = 1 Ω	-	7	15	ns
Rise time	t _r		-	21	40	
Turn-off delay time	t _{d(off)}		-	11	20	
Fall time	t _f		-	11	20	
Turn-on delay time	t _{d(on)}	V _{DD} = -10 V, R _L = 33.3 Ω, I _D ≅ -0.3 A, V _{GEN} = -8 V, R _g = 1 Ω	-	2	5	
Rise time	t _r		-	18	40	
Turn-off delay time	t _{d(off)}		-	10	20	
Fall time	t _f		-	10	20	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I _S	T _A = 25 °C	-	-	-0.5 ^c	A
Pulse diode forward current	I _{SM}		-	-	-0.8	
Body diode voltage	V _{SD}	I _S = -0.3 A, V _{GS} = 0 V	-	-0.9	-1.2	V
Body diode reverse recovery time	t _{rr}	I _F = -0.3 A, dI/dt = 100 A/μs, T _J = 25 °C	-	15	30	ns
Body diode reverse recovery charge	Q _{rr}		-	7.5	15	nC
Reverse recovery fall time	t _a		-	10.5	-	ns
Reverse recovery rise time	t _b		-	4.5	-	

Notes

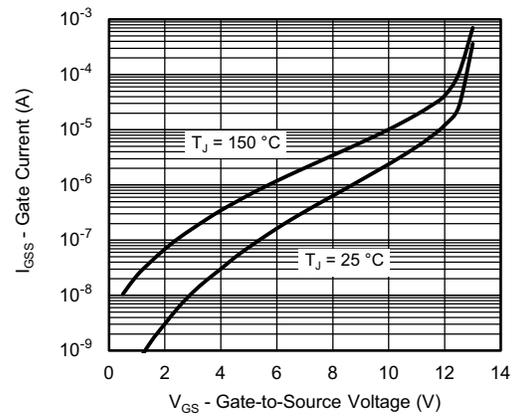
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Surface mounted on 1" x 1" FR4 board with full copper, t = 5 s.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

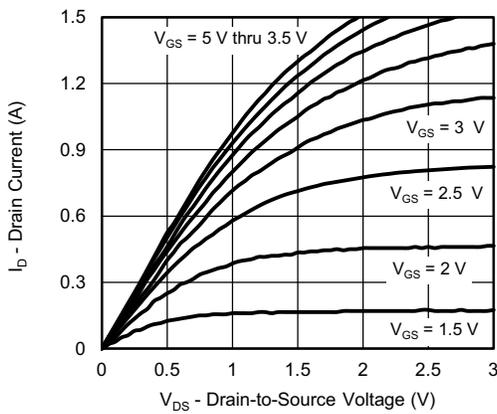
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



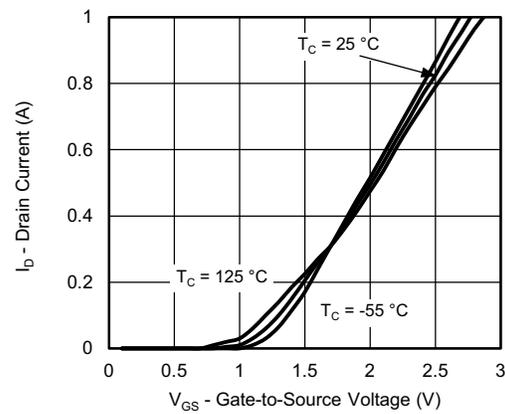
Gate Current vs. Gate-Source Voltage



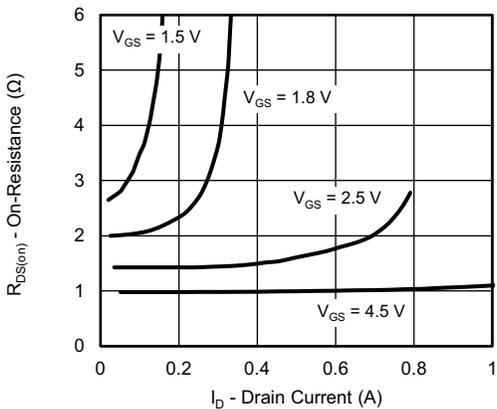
Gate Current vs. Gate-Source Voltage



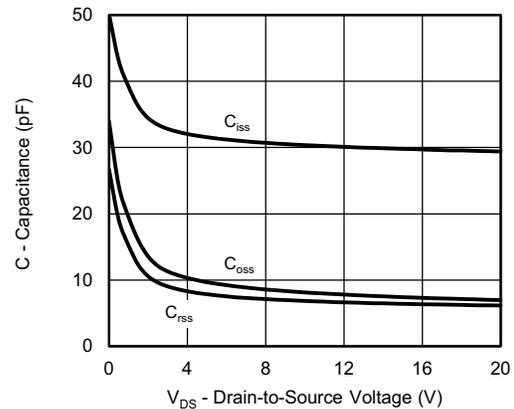
Output Characteristics



Transfer Characteristics

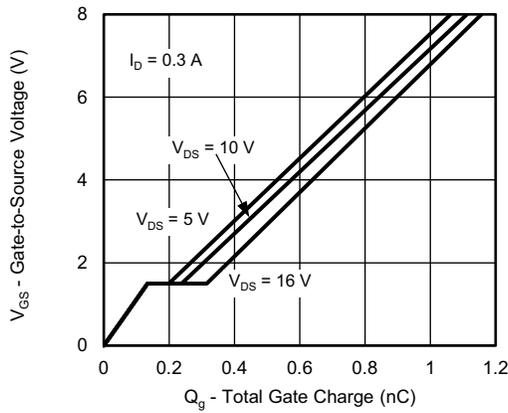


On-Resistance vs. Drain Current and Gate Voltage

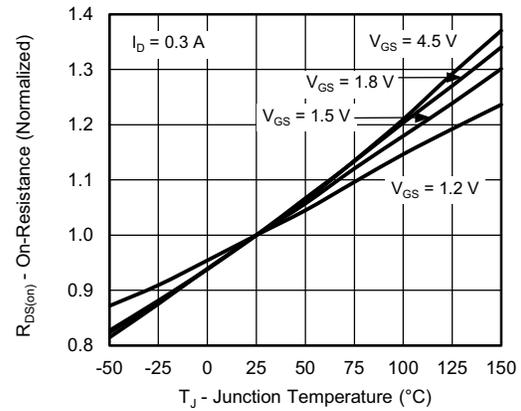


Capacitance

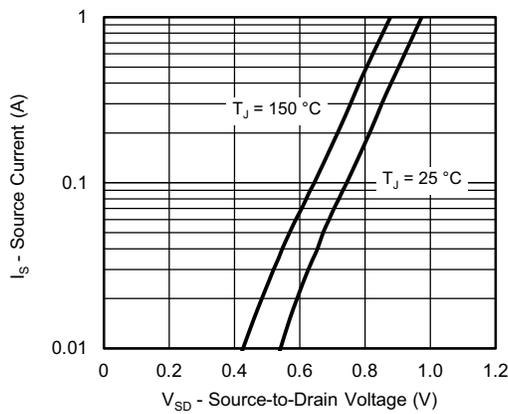
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



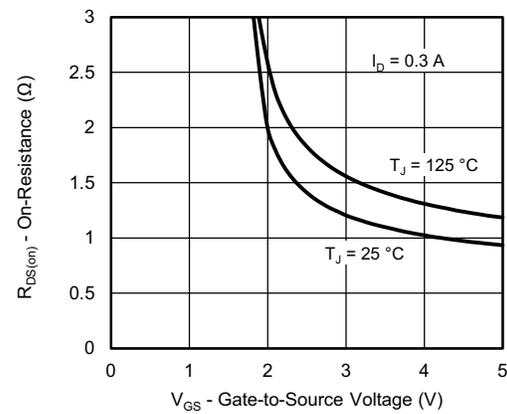
Gate Charge



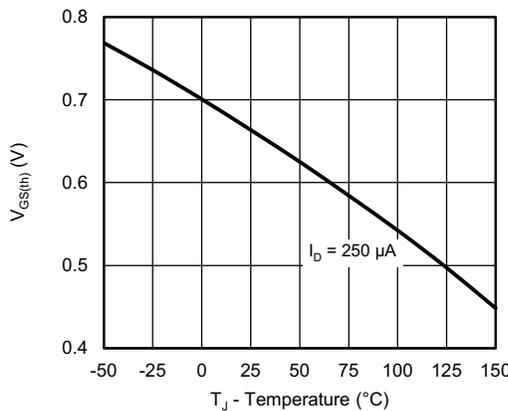
On-Resistance vs. Junction Temperature



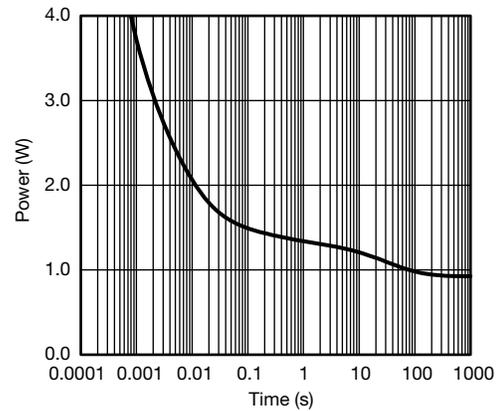
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



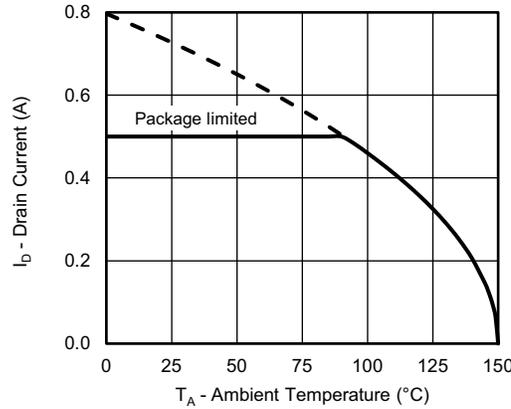
Threshold Voltage



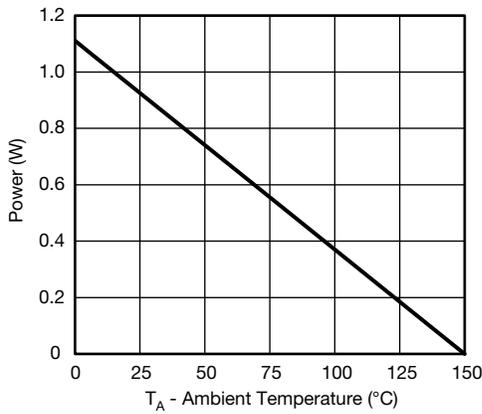
Single Pulse Power, Junction-to-Ambient



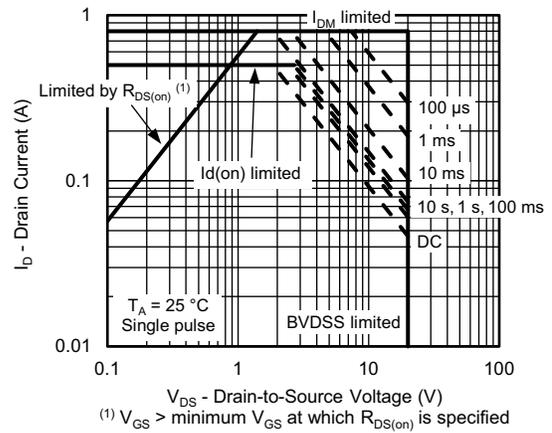
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a



Power, Junction-to-Ambient



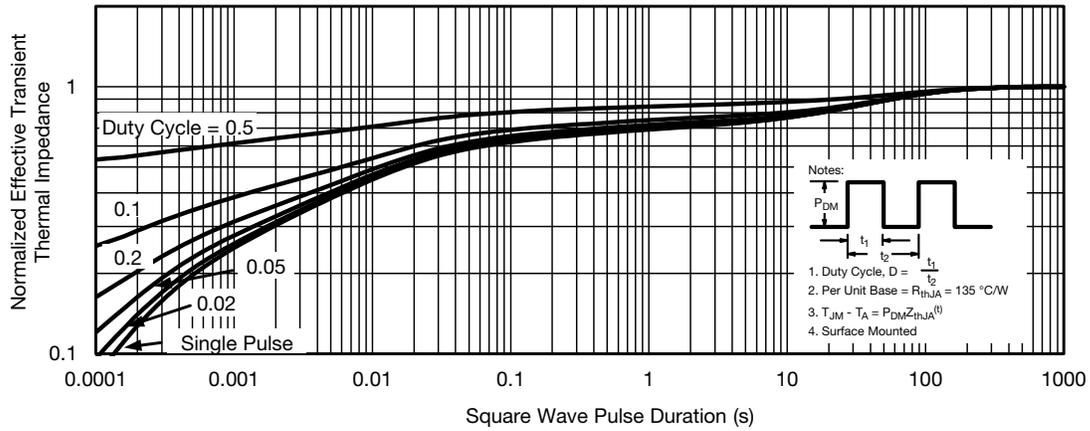
Safe Operating Area, Junction-to-Ambient

Note

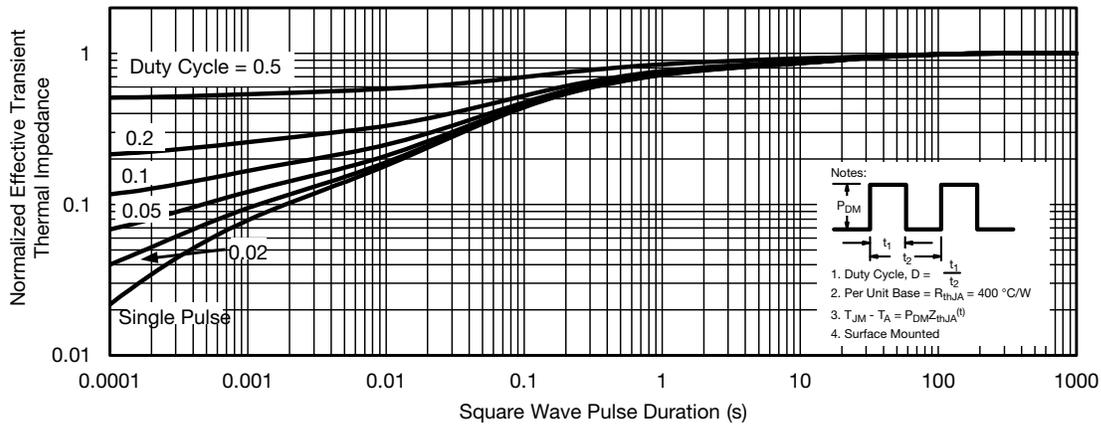
- a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-ambient thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient (on 1" x 1" FR4 board with maximum copper)



Normalized Thermal Transient Impedance, Junction-to-Ambient (on 1" x 1" FR4 board with minimum copper)

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